

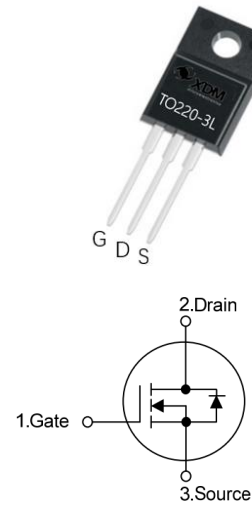
10A, 650V N-CHANNEL POWER MOSFET

Features

- $R_{DS(on)}=1.0\Omega(\text{Max.}) @V_{GS}=10V, I_D=5A$
- Low gate charge
- Low Ciss
- Fast switching

Applications

- LED Power Supplies
- Cell Phone Charger
- Standby Power



Key Performance and Package Parameters

Order codes	V_{DS}	I_D	$R_{DS(ON)}$, Typ	T_{vjmax}	Marking	Package
XD010M065BX1H3	650V	10A	0.85Ω	150°C	D10M65BX1	TO220F-3L

Absolute Maximum Ratings ($T_c=25^\circ\text{C}$ unless otherwise noted.)

Symbol	Parameter	Value	Units
V_{DSS}	Drain-Source Voltage	650	V
V_{GSS}	Gate-Source Voltage	± 30	V
I_D	Continuous Drain Current ($T_c=25^\circ\text{C}$)	10	A
	Continuous Drain Current ($T_c=100^\circ\text{C}$)	4.4	A
I_{DM}	Pulsed Drain Current	40	A
P_D	Maximum Power Dissipation ($T_c=25^\circ\text{C}$)	40	W
	Maximum Power Dissipation ($T_c=100^\circ\text{C}$)	16	W
E_{AS}	Avalanche Energy, Single pulse($L=30\text{mH}$) (note1)	435	mJ
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Max.	Units
$R_{\theta JC}$	Thermal Resistance-Junction to case (Steady State)	3.13	$^\circ\text{C/W}$

Electrical Characteristics ($T_c=25^{\circ}\text{C}$ unless otherwise noted.)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_{DS}=250\mu A$	650	---	---	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=650V, V_{GS}=0V$	---	1.0	2.0	μA
I_{GSS}	Gate Leakage Current, Forward	$V_{GS}=30V, V_{DS}=0V$	---	---	100	nA
	Gate Leakage Current, Reverse	$V_{GS}=-30V, V_{DS}=0V$	---	---	-100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_{DS}=250\mu A$	2	3	4	V
$R_{DS(ON)}$	Drain-Source On-state Resistance	$V_{GS}=10V, I_{DS}=5A$	--	0.85	1.0	Ω
Qg	Total Gate Charge	$V_{DS}=520V$	---	28.7	---	nC
Qgs	Gate-Source Charge	$V_{GS}=10V$	---	10.3	---	nC
Qgd	Gate-Drain Charge	$I_{DS}=10A$	---	6.8	---	nC
$t_{d(on)}$	Turn-on Delay Time	$V_{DD}=325V, V_{GE}=10V$ $I_{DS}=10A, R_G=10\Omega$	---	16	---	nS
t_r	Turn-on Rise Time		--	29	--	nS
$t_{d(off)}$	Turn-off Delay Time		---	34	---	nS
t_f	Turn-off Fall Time		---	29	---	nS
C_{iss}	Input Capacitance	$V_{DS}=25V$	---	1650	---	pF
C_{oss}	Output Capacitance	$V_{GS}=0V$	---	120	---	pF
C_{rss}	Reverse Transfer Capacitance	$f=1\text{MHz}$	---	27	---	pF

Diode Characteristics of Diode ($T_c=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
V_{SD}	Diode Forward Voltage	$I_{SD}=10A, V_{GS}=0V$	---	0.85	1.5	V
t_{rr}	Diode Reverse Recovery Time	$V_{DS}=30V, I_{SD}=1A,$	---	142	---	ns
Q_{rr}	Diode Reverse Recovery Charge	$di_{SD}/dt=100A/\mu s$	---	475	---	nC

Notes:

1. $L=30\text{mH}, V_{DD}=50V, R_G=25\Omega$, Starting $T_J=25^{\circ}\text{C}$.

Typical Characteristics

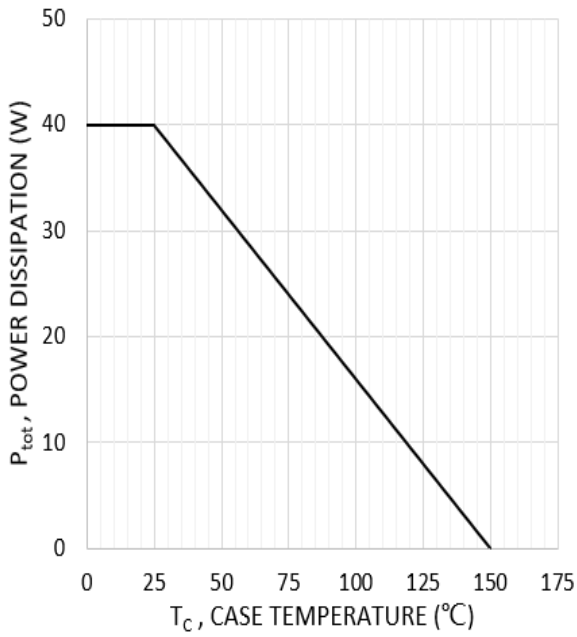


Fig.1 Power Dissipation

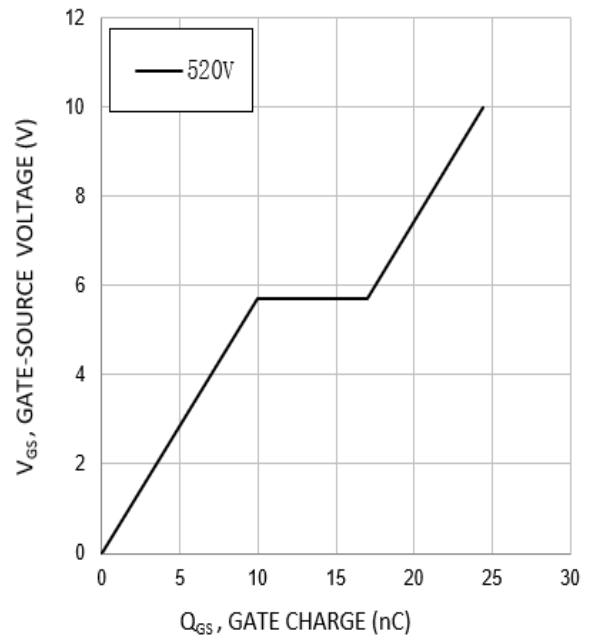


Fig.2 Gate Charge

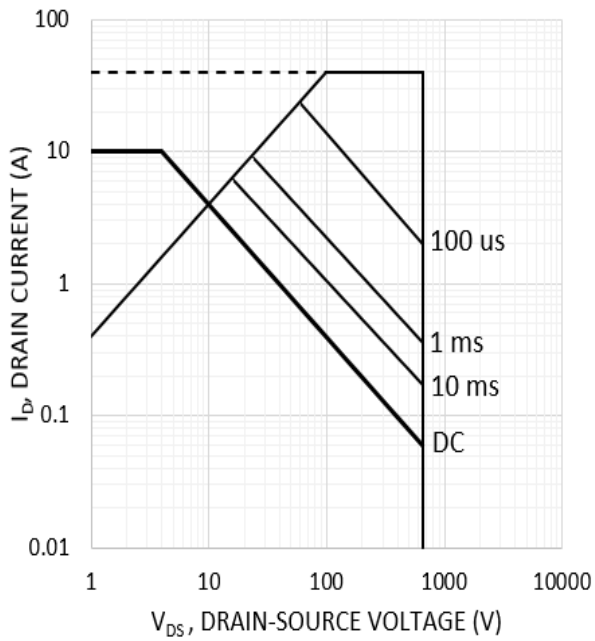


Fig.3 Safe Operation Area

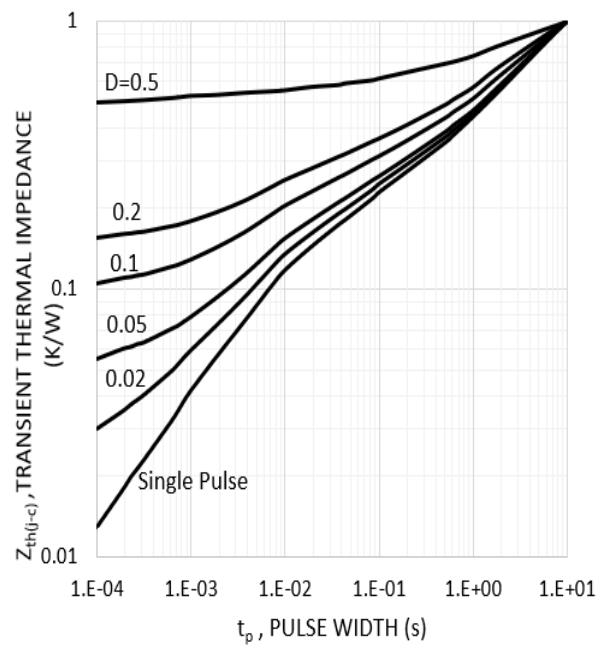


Fig.4 Thermal Transient Impedance

Typical Characteristics

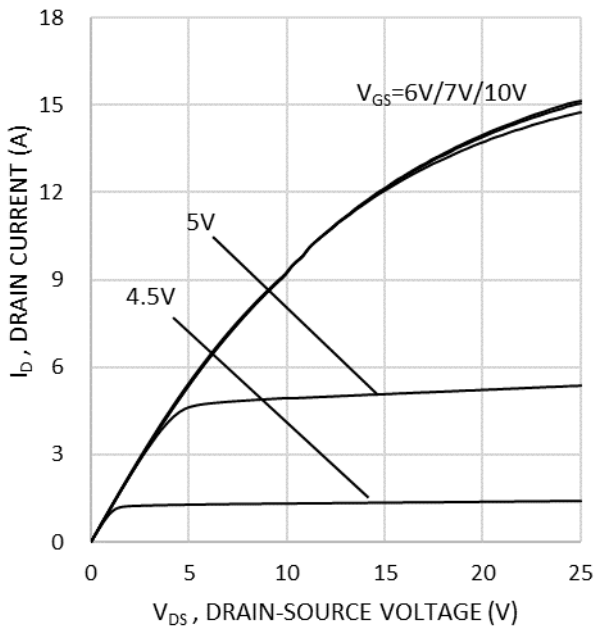


Fig.5 Output Characteristics

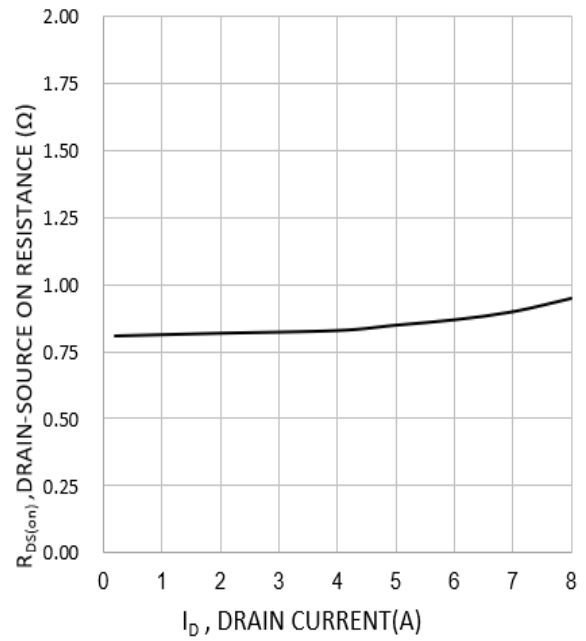


Fig.6 Drain-Source On Resistance

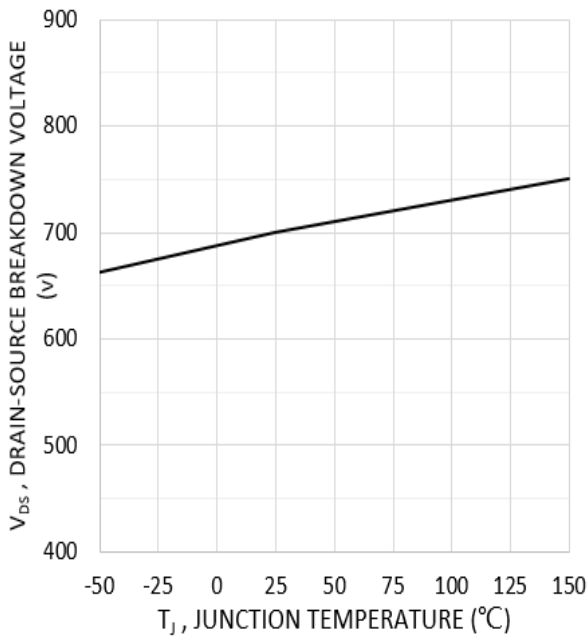


Fig.7 Drain-Source Breakdown Voltage

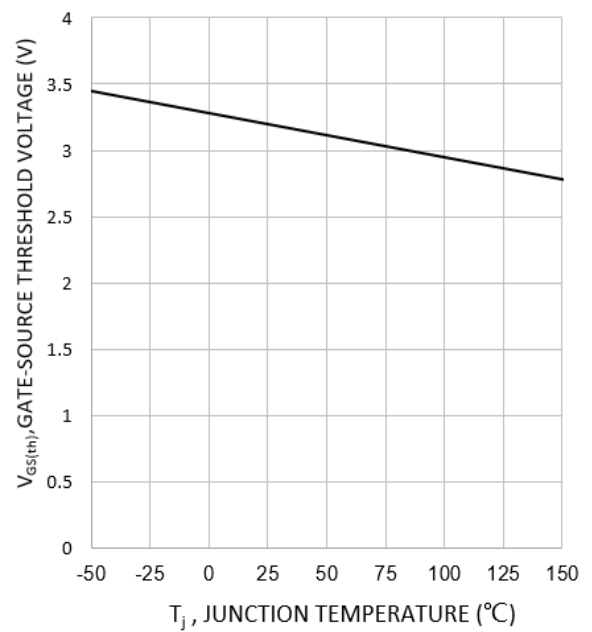


Fig.8 Gate Threshold Voltage

Typical Characteristics

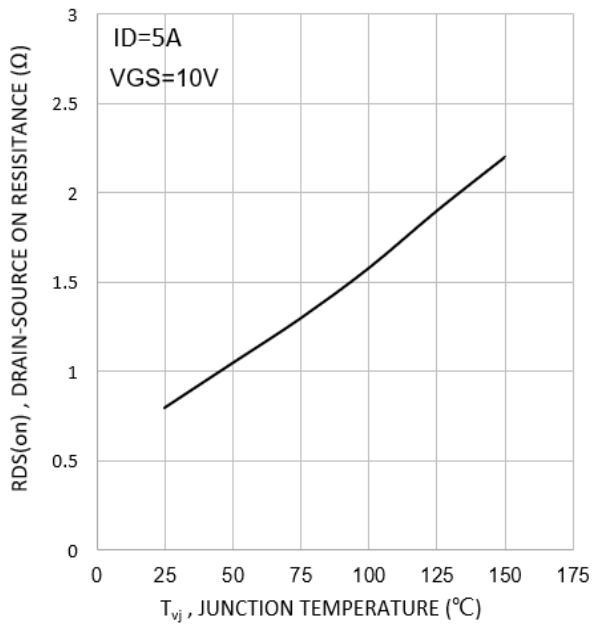


Fig.9 Drain-Source On Resistance

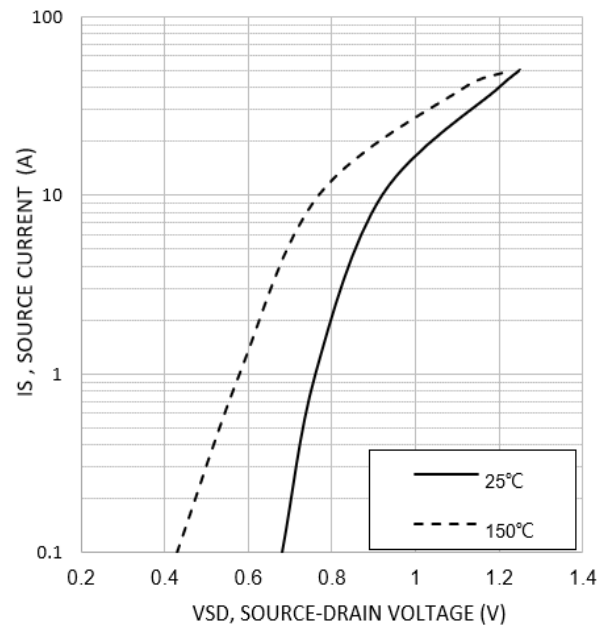


Fig.10 Source-Drain Diode Forward

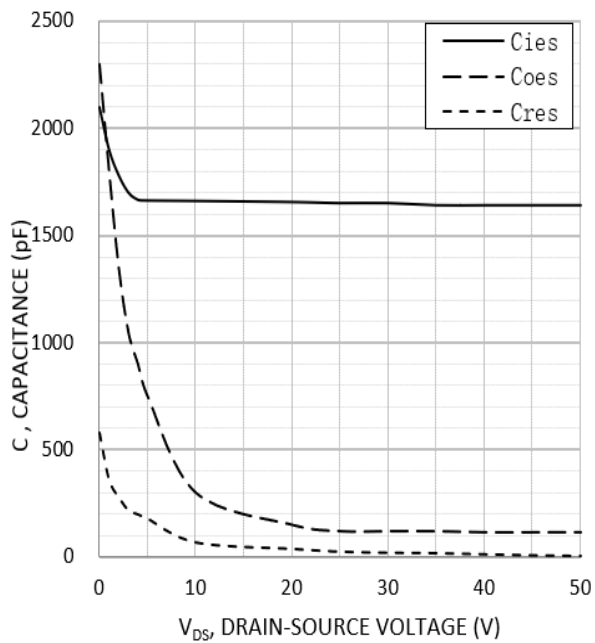
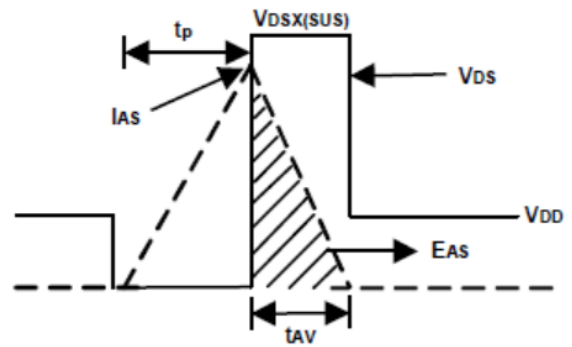
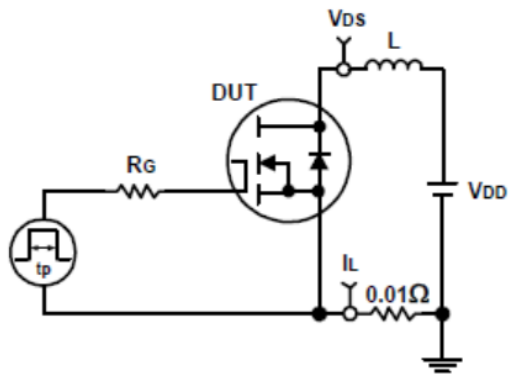
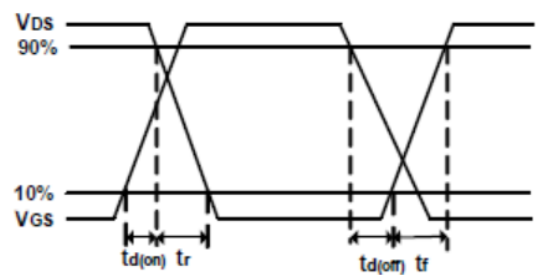
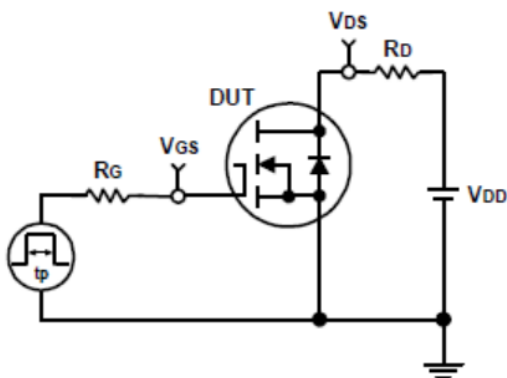


Fig.11 Capacitance

Avalanche Test Circuit and Waveforms

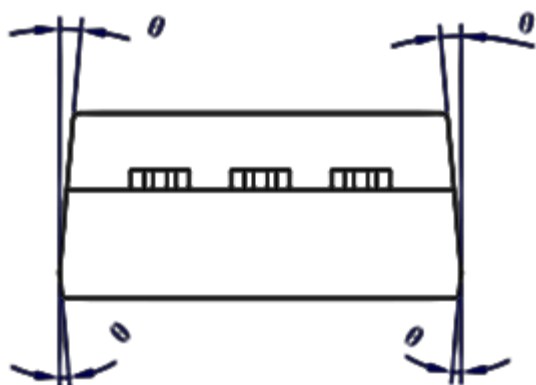
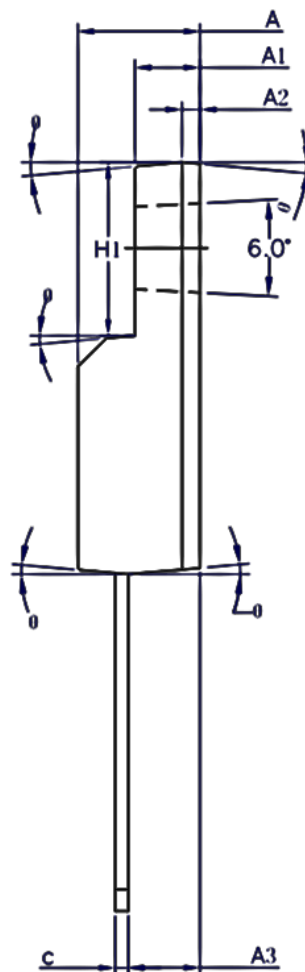
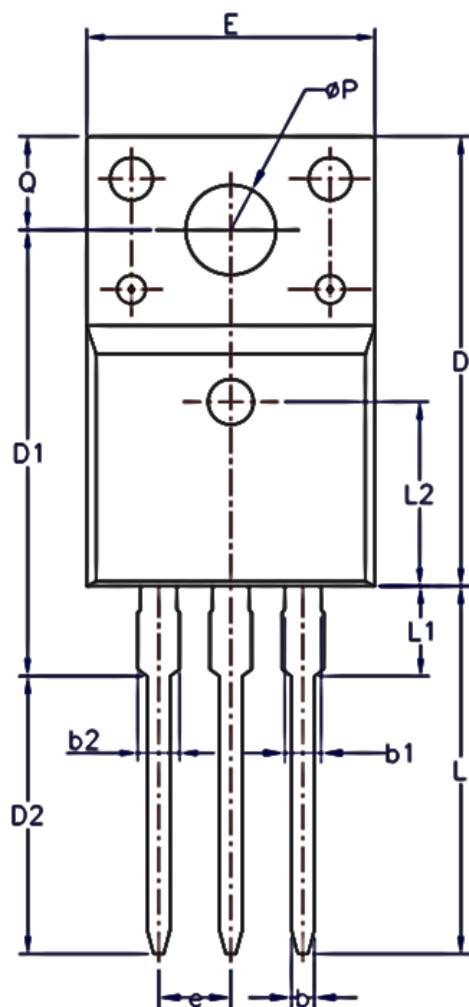


Switching Time Test Circuit and Waveforms



Package Information

TO-220F-3L



SYMBOL	MIN	NOM	MAX
A	4.50	4.70	4.83
A1	2.34	2.54	2.74
A2	0.70 REF		
A3	2.56	2.76	2.93
b	0.70	-	0.90
b1	1.18	-	1.38
b2	-	-	1.47
c	0.45	0.50	0.60
D	15.67	15.87	16.07
D1	15.55	15.75	15.95
D2	9.60	9.80	10.0
E	9.96	10.16	10.36
e	2.54BSC		
H1	6.48	6.68	6.88
L	12.68	12.98	13.28
L1	-	-	3.50
L2	6.50REF		
øP	3.08	3.18	3.28
Q	3.20	-	3.40
θ1	1°	3°	5°

Revision History

Ver.	Date	Change Notice
1.0	2022/05/17	Release